



60V NPN LOW VCESAT TRANSISTOR IN PowerDI3333-8

Features

- BVcEo > 60V
- Small Form Factor Thermally Efficient Package.
 Enables Higher Density End Products
- Ic = 6A Continuous Collector Current
- Icm = 20A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 60mV @ 1A
- h_{FE} Specified up to 10A for a High Gain Hold up
- Complementary PNP Type: DXTP03060BFG
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)

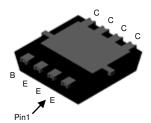
Applications

- MOSFET & IGBT Gate Drivers
- Solenoid, Relay And Actuator Drivers
- DC to DC Converters
- Motor Control

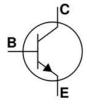
PowerDI3333-8 (SWP) (Type UX)



Top View



Bottom View



Device Symbol

Ordering Information (Note 4)

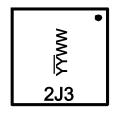
Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DXTN03060BFG-7	Standard	2J3	7	12	2,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8 (SWP) (Type UX)



2J3= Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 21 = 2021) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	VcBo	100	V
Collector-Emitter Voltage	VCEO	60	V
Emitter-Base Voltage	VEBO	7	V
Continuous Collector Current	Ic	6	A
Peak Pulse Current	Ісм	20	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	PD	1.2	W
Power Dissipation	(Note 6)	PD	2.7	W
Thermal Desistance Lunction to Ambient	(Note 5)	Devi	107	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	48	°C/W
Thermal Resistance, Junction to Leads (Note 7	ReJL	8.5	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Charge Device Model	CDM	1,000	V	C5

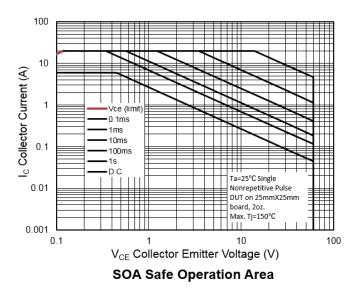
Notes:

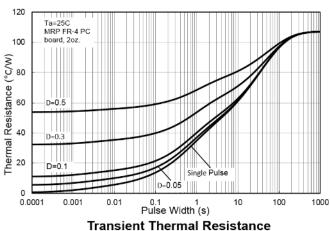
- 5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state.

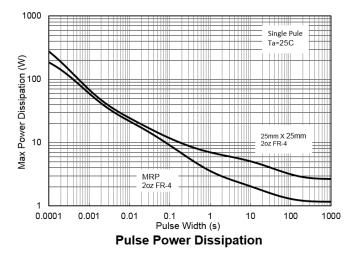
 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Thermal resistance from junction to solder-point (at the collector tab).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

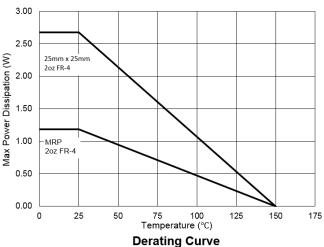


Thermal Characteristics and Derating Information











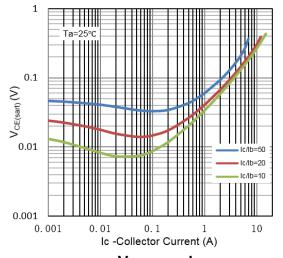
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	100	198	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BVceo	60	79	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.4	_	V	IE = 100μA
Collector Cut-off Current		_	2	50	nA	V _{CB} = 100V
Collector Gut-on Gurrent	Ісво	_	0.05	10	μΑ	$V_{CB} = 100V, T_A = +125^{\circ}C$
Collector Cut-off Current	ICER	_	5	100	nA	V _{CB} = 60V
Collector Gut-on Gurrent	R _B ≤ 1kΩ	_	0.2	10	μΑ	$V_{CB} = 60V, T_A = +125$ °C
Emitter Cut-off Current	I _{EBO}	1	1	20	nA	V _{EB} = 6V
		100	197	_	_	$I_C = 10mA$, $V_{CE} = 2V$
		100	195	400	_	IC = 1A, VCE = 2V
DC Current Gain (Note 9)	hFE	100	194	300	_	IC = 2A, VCE = 2V
		55	117	_	_	IC = 5A, VCE = 2V
		20	50	_	_	IC = 10A, VCE = 2V
		_	15	30	mV	Ic = 100mA, I _B = 5mA
		_	35	60	mV	I _C = 1A, I _B = 100mA
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	_	42	70	mV	$I_C = 1A$, $I_B = 50mA$
		_	86	135	mV	Ic = 2A, I _B = 50mA
		_	176	260	mV	Ic = 6A, I _B = 300mA
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	986	1100	mV	Ic = 6A, I _B = 300mA
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	_	916	1000	mV	Ic = 6A, VcE = 1V
Input Capacitance	C _{ibo}	_	563	_	pF	V _{EB} = 0.5V. f = 1MHz
Output Capacitance	Cobo	_	26	_	pF	V _{CB} = 10V. f = 1MHz
Current Gain-Bandwidth Product	fτ	_	140	_	MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz
	t _{delay}	_	17.9	_	ns	
Switching Time	t _{rise}		6.1	_	ns	Ic = 1A, Vcc = 10V,
Switching fille	t _{storage}	_	1256	_	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$
	t _{fall}		27.6	_	ns	

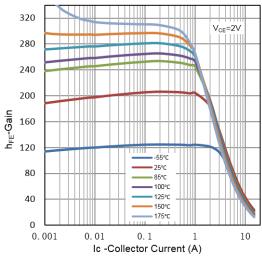
Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



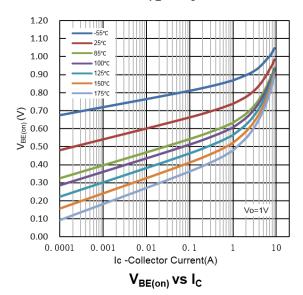
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

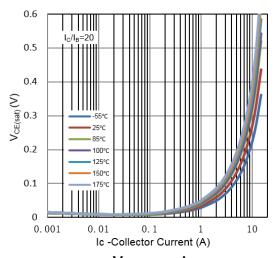


$V_{\text{CE(sat)}} vs I_{\text{C}}$

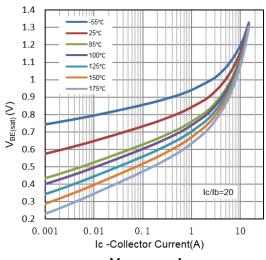


 h_{FE} vs I_{C}

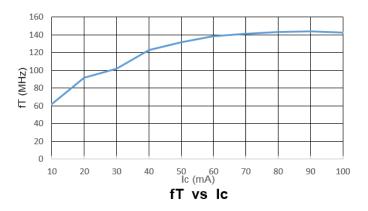




 $V_{\text{CE(sat)}} vs I_{\text{C}}$



 $V_{\text{BE(sat)}} vs I_{\text{C}}$

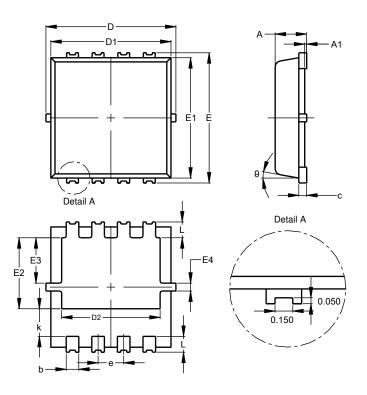




Package Outline Dimensions

Please see https://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

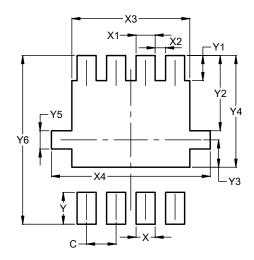


PowerDI3333-8 (SWP)						
	(Type UX)					
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
E	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see https://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Υ	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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